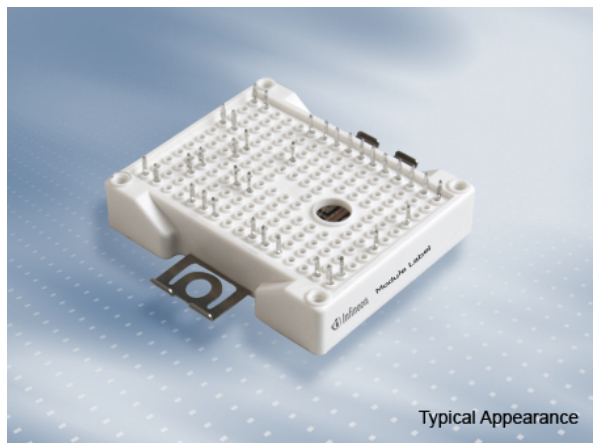


$V_{CES} = 1200V$

$I_{C\ nom} = 40A / I_{CRM} = 80A$

典型应用

- 太阳能应用

电气特性

- 高速IGBT H3
- 低开关损耗

机械特性

- 3 kV 交流 1分钟 绝缘
- 低热阻的三氧化二铝 (Al_2O_3) 衬底
- 集成NTC温度传感器
- 紧凑型设计
- PressFIT 压接技术

Typical Applications

- Solar applications

Electrical Features

- High speed IGBT H3
- Low switching losses

Mechanical Features

- 3 kV AC 1min insulation
- Al_2O_3 substrate with low thermal resistance
- Integrated NTC temperature sensor
- Compact design
- PressFIT contact technology

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

prepared by: CM	date of publication: 2016-04-04	
approved by: AKDA	revision: V3.1	UL approved (E83335)

反极性保护二极管A / Inverse-polarity protection diode A

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
最大正向均方根电流(每芯片) Maximum RMS forward current per chip	$T_C = 80^{\circ}\text{C}$	I_{FRMSM}	50	A
最大整流器输出均方根电流 Maximum RMS current at rectifier output	$T_C = 80^{\circ}\text{C}$	I_{RMSM}	60	A
正向浪涌电流 Surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I_{FSM}	360 290	A A
I^2t -值 I^2t - value	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	650 420	A^2s A^2s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$T_{vj} = 150^{\circ}\text{C}, I_F = 30\text{ A}$	V_F		0,95		V
反向电流 Reverse current	$T_{vj} = 150^{\circ}\text{C}, V_R = 1200\text{ V}$	I_R		0,10		mA
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode	R_{thJC}		0,800	0,900	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}		0,800		K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

反极性保护二极管B / Inverse-polarity protection diode B

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
最大正向均方根电流(每芯片) Maximum RMS forward current per chip	$T_C = 80^{\circ}\text{C}$	I_{FRMSM}	30	A
最大整流器输出均方根电流 Maximum RMS current at rectifier output	$T_C = 80^{\circ}\text{C}$	I_{RMSM}	60	A
正向浪涌电流 Surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I_{FSM}	290 245	A A
I^2t -值 I^2t - value	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	420 300	A^2s A^2s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$T_{vj} = 150^{\circ}\text{C}, I_F = 20\text{ A}$	V_F		1,00		V
反向电流 Reverse current	$T_{vj} = 150^{\circ}\text{C}, V_R = 1200\text{ V}$	I_R		0,10		mA
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode	R_{thJC}		1,20	1,35	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}		1,15		K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

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IGBT, 斩波器 / IGBT-Chopper

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_C = 75^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$	$I_{C\text{ nom}}$ I_C	40 50	A A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	80	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$	P_{tot}	180	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 40\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 40\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	2,05 2,50 2,60	2,40	V V V
栅极阈值电压 Gate threshold voltage	$I_C = 1,00\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,00	5,80	6,50 V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	0,32		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,0		Ω
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	2,35		nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,13		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		100	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 40\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 12\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{ on}}$	0,035 0,035 0,035		μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 40\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 12\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,02 0,025 0,025		μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 40\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 12\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{ off}}$	0,23 0,29 0,31		μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 40\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 12\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,02 0,04 0,05		μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 40\text{ A}, V_{CE} = 600\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 1800\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 12\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	2,00 3,10 3,50		mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 40\text{ A}, V_{CE} = 600\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 4300\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 12\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	1,50 2,40 2,70		mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CE\text{ max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\text{ }\mu\text{s}, T_{vj} = 125^{\circ}\text{C}$		I_{SC}	130		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}	0,550	0,700	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,550		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

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Diode-斩波器 / Diode-Chopper

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	25	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	30	A
I2t-值 I²t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	310	A²s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 25\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 25\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 25\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	2,00 1,70 1,65	2,55	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 25\text{ A}, -di_F/dt = 1600\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	30,0 45,0 50,0		A A A
恢复电荷 Recovered charge	$I_F = 25\text{ A}, -di_F/dt = 1600\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	1,50 3,50 4,00		μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 25\text{ A}, -di_F/dt = 1600\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	0,70 1,75 2,15		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}	0,700	0,750	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,700		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	°C

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

			min.	typ.	max.	
额定电阻值 Rated resistance	$T_{NTC} = 25^{\circ}\text{C}$	R_{25}		5,00		kΩ
R100 偏差 Deviation of R100	$T_{NTC} = 100^{\circ}\text{C}, R_{100} = 493\text{ }\Omega$	$\Delta R/R$	-5		5	%
耗散功率 Power dissipation	$T_{NTC} = 25^{\circ}\text{C}$	P_{25}			20,0	mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$		3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$		3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$		3433		K

根据应用手册标定

Specification according to the valid application note.

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模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	3,0	kV
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃	
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		11,5 6,3	mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		10,0 5,0	mm
相对电痕指数 Comperative tracking index		CTI	> 200	
杂散电感, 模块 Stray inductance module		L _{sCE}	min. 25	typ. max. nH
储存温度 Storage temperature		T _{stg}	-40	125 °C
Anpresskraft für mech. Bef. pro Feder mounting force per clamp		F	40	- 80 N
重量 Weight		G	36	g

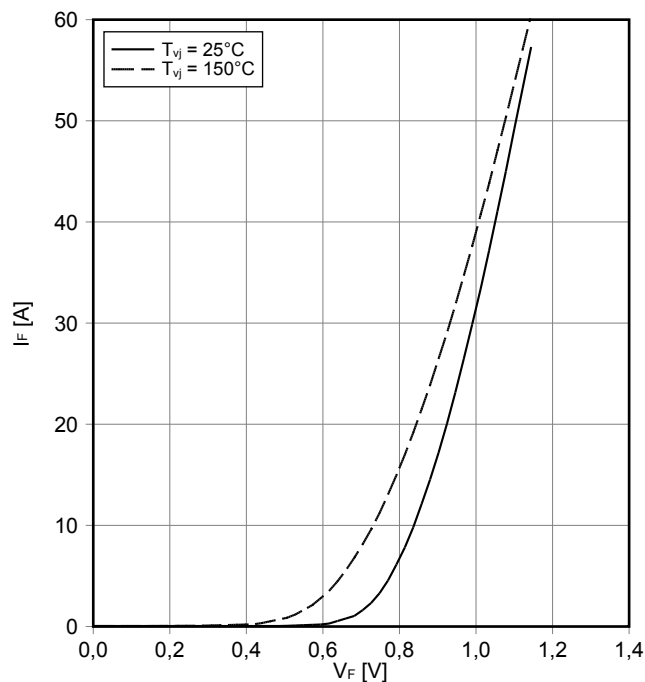
Der Strom im Dauerbetrieb ist auf 25A effektiv pro Anschlusspin begrenzt.
The current under continuous operation is limited to 25A rms per connector pin.

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正向偏压特性 反极性保护二极管A (典型)

forward characteristic of Inverse-polarity protection diode A (typical)

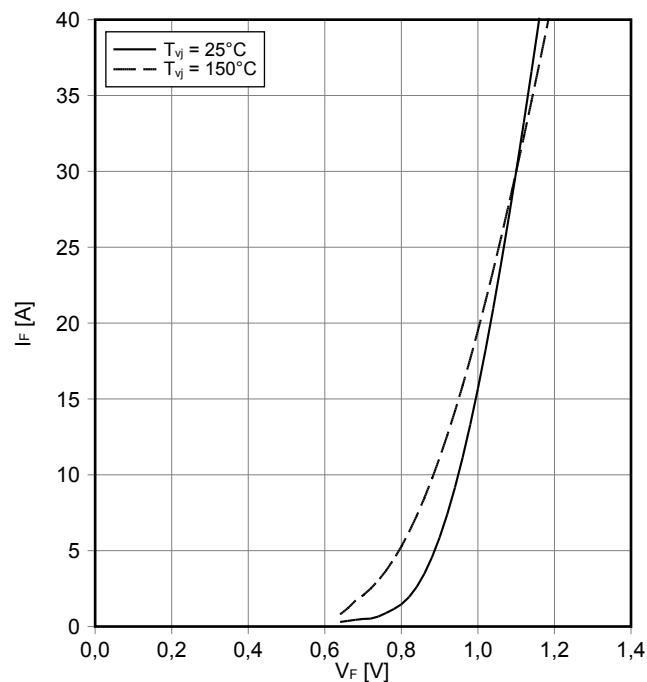
$I_F = f(V_F)$



正向偏压特性 反极性保护二极管B (典型)

forward characteristic of Inverse-polarity protection diode B (typical)

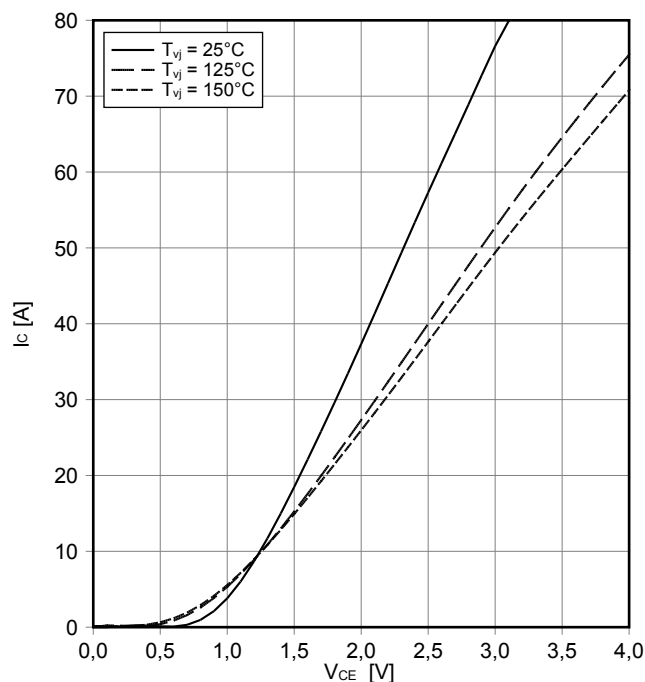
$I_F = f(V_F)$



输出特性 IGBT, 斩波器 (典型)

output characteristic IGBT-Chopper (typical)

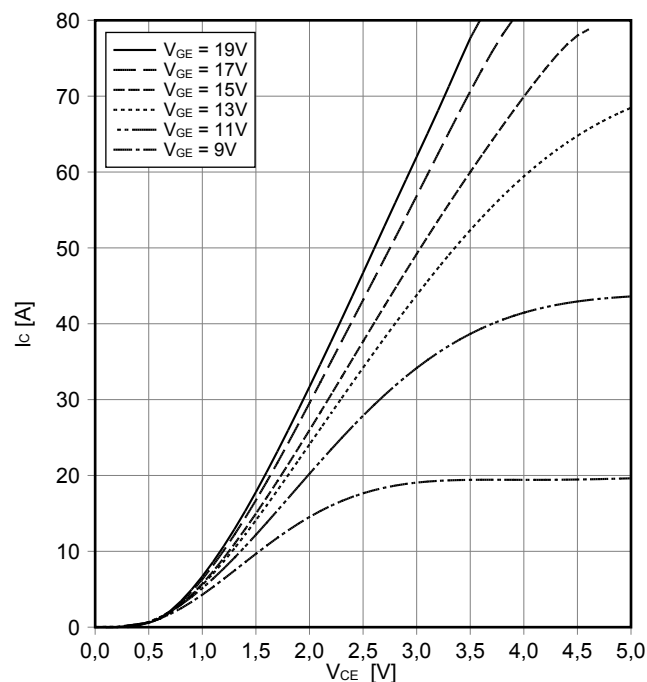
$I_C = f(V_{CE})$
 $V_{GE} = 15 \text{ V}$



输出特性 IGBT, 斩波器 (典型)

output characteristic IGBT-Chopper (typical)

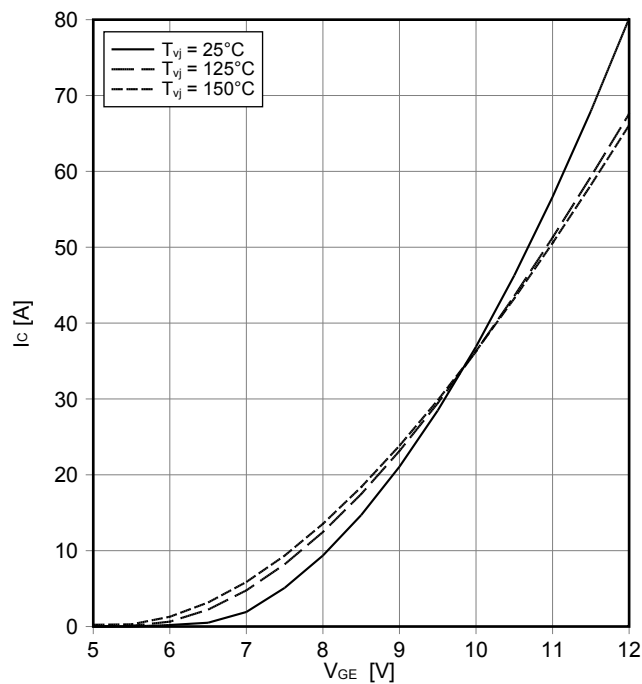
$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



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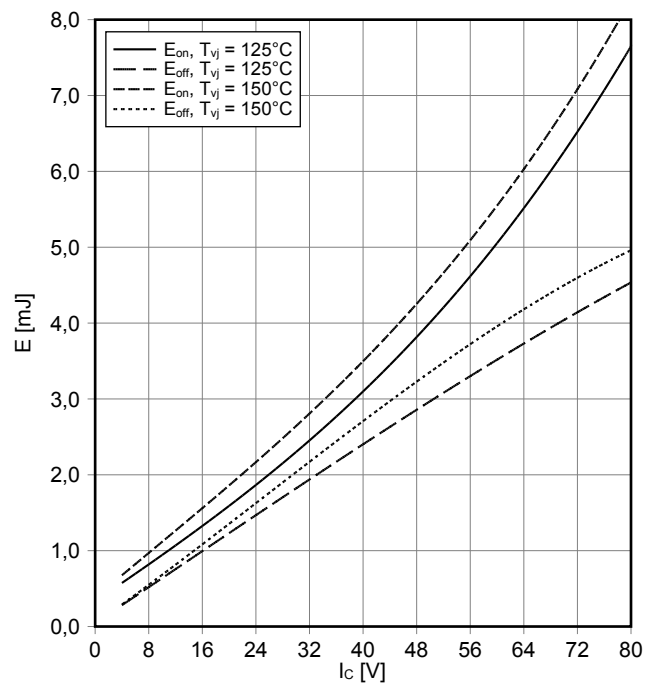
传输特性 IGBT, 斩波器 (典型)
transfer characteristic IGBT-Chopper (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



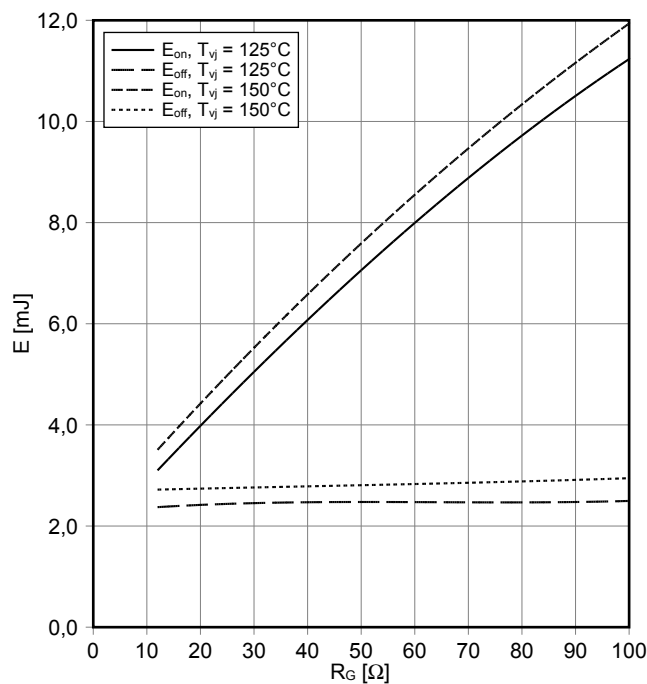
开关损耗 IGBT, 斩波器 (典型)
switching losses IGBT-Chopper (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 12\ \Omega$, $R_{Goff} = 12\ \Omega$, $V_{CE} = 600\text{ V}$



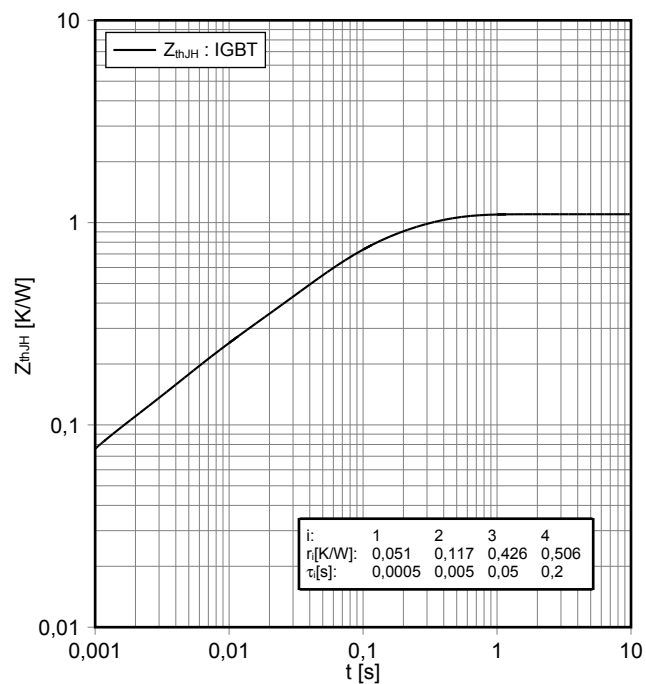
开关损耗 IGBT, 斩波器 (典型)
switching losses IGBT-Chopper (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 40\text{ A}$, $V_{CE} = 600\text{ V}$



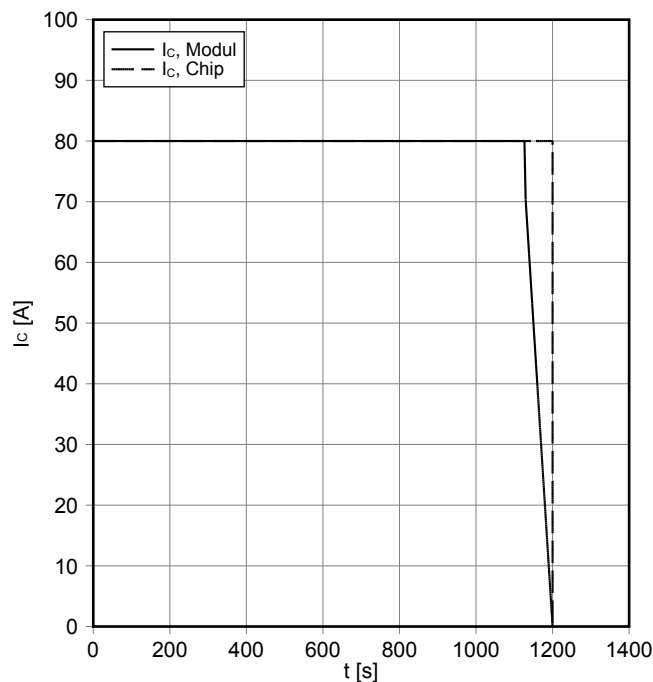
瞬态热阻抗 IGBT, 斩波器
transient thermal impedance IGBT-Chopper

$Z_{thJH} = f(t)$



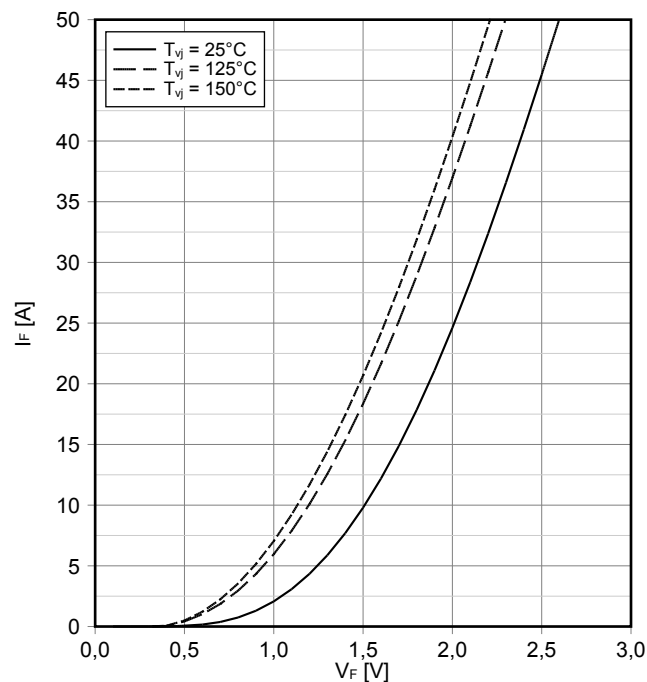
反偏安全工作区 IGBT, 斩波器 (RBSOA)
reverse bias safe operating area IGBT-Chopper (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15 \text{ V}$, $R_{Goff} = 12 \Omega$, $T_{vj} = 150^\circ\text{C}$



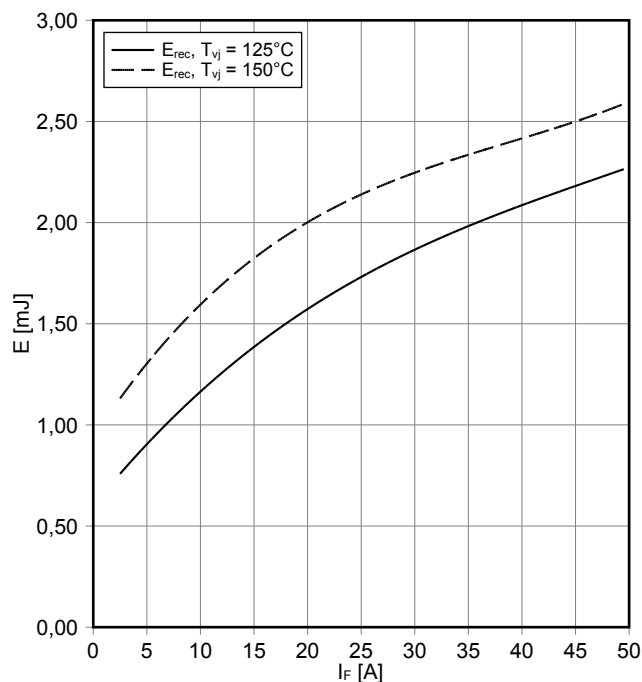
正向偏压特性 Diode-斩波器 (典型)
forward characteristic of Diode-Chopper (typical)

$I_F = f(V_F)$



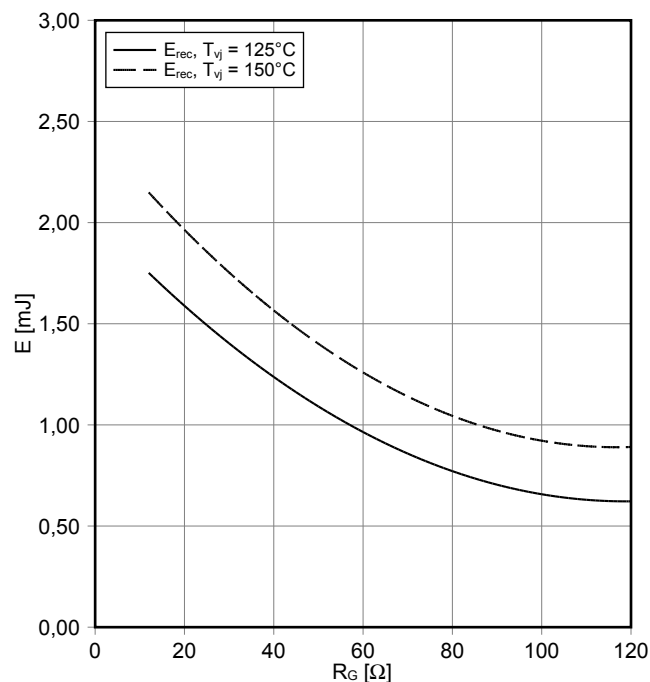
开关损耗 Diode-斩波器 (典型)
switching losses Diode-Chopper (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 12 \Omega$, $V_{CE} = 600 \text{ V}$



开关损耗 Diode-斩波器 (典型)
switching losses Diode-Chopper (typical)

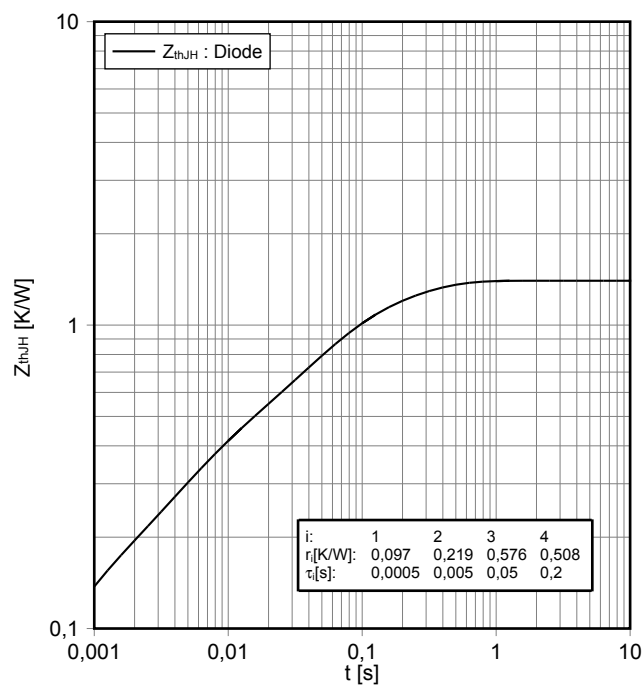
$E_{rec} = f(R_G)$
 $I_F = 25 \text{ A}$, $V_{CE} = 600 \text{ V}$



瞬态热阻抗 Diode-斩波器

transient thermal impedance Diode-Chopper

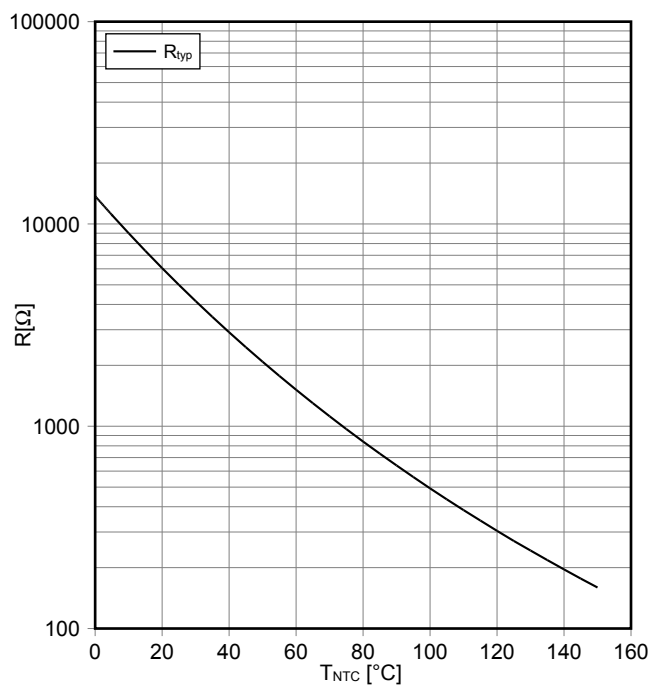
$Z_{thJH} = f(t)$



负温度系数热敏电阻 温度特性

NTC-Thermistor-temperature characteristic (typical)

$R = f(T)$



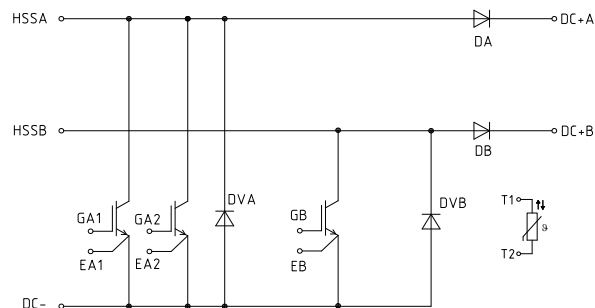
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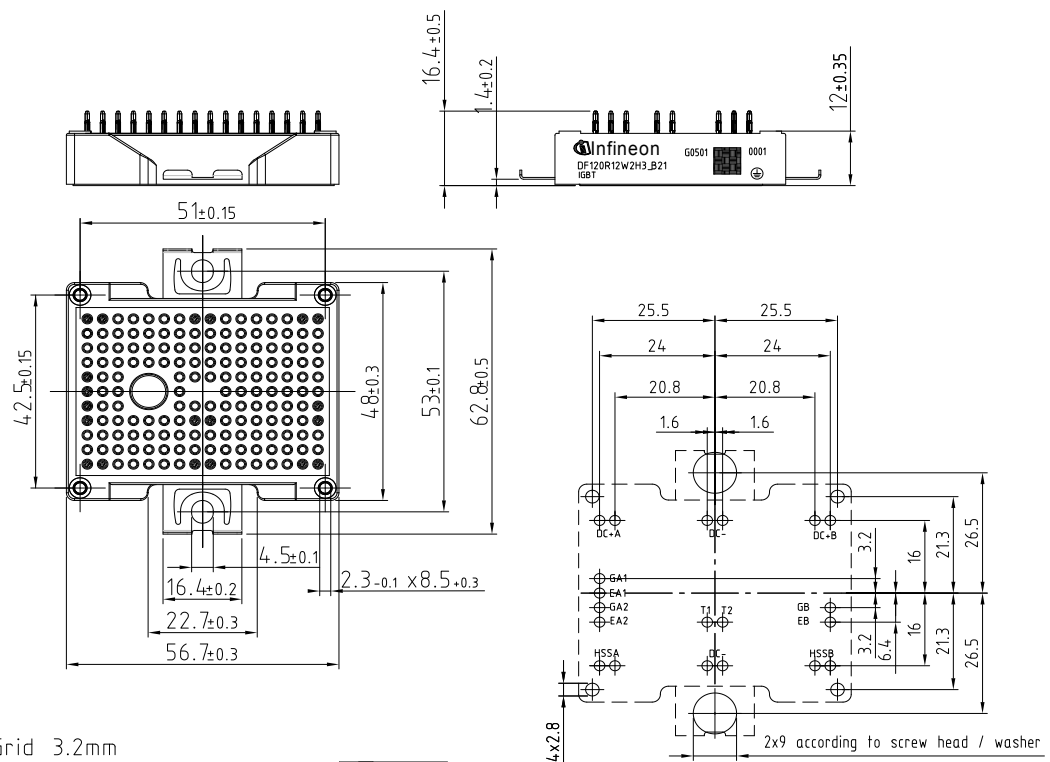
approved by: AKDA

revision: V3.1

接线图 / Circuit diagram



封装尺寸 / Package outlines



- Pin-Grid 3.2mm
- Tolerance of PCB hole pattern ± 0.1
- Hole specification for contacts see AN 2009-09
- Diameters of plated holes ϕ 1.0mm
- Diameters of drill ϕ 1.15mm

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